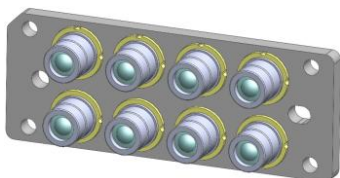


Laser Diode LT-LD-465-33W-A



LT-LD-465-33W-A is a high-power multiple laser diode (LD) bank with 33W CW output power at 465nm. It is supplied in a bank mounted can with Zener Diode. The laser diode is suitable for the use in various opto-electronic applications.

■ Absolute Maximum Ratings ($T_c=22^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Forward Current	I_f	3.5	A
Reverse Current	$I_{R(LD)}$	85	mA
Storage Temperature	T_{stg}	-40~85	$^{\circ}\text{C}$
Operating Temperature	T_{mc}	0~70	$^{\circ}\text{C}$

■ Initial Electrical/Optical Characteristics of LD Bank ($T_c=22^{\circ}\text{C}$)

Parameter	Symbol	Condition	Min	Typ.	Max	Unit
Optical Output Power	P_o	$I_f = 3.0\text{A}$	30	33	-	W
Dominant Wavelength	λ_d	$I_f = 3.0\text{A}$	458	(465)	472	nm
Operating Voltage	V_{op}	$I_f = 3.0\text{A}$	29	(33)	37	V
Beam Pointing Tilt Angle	$\Delta\theta$	$I_f = 3.0\text{A}$	-	-	0.7	$^{\circ}$

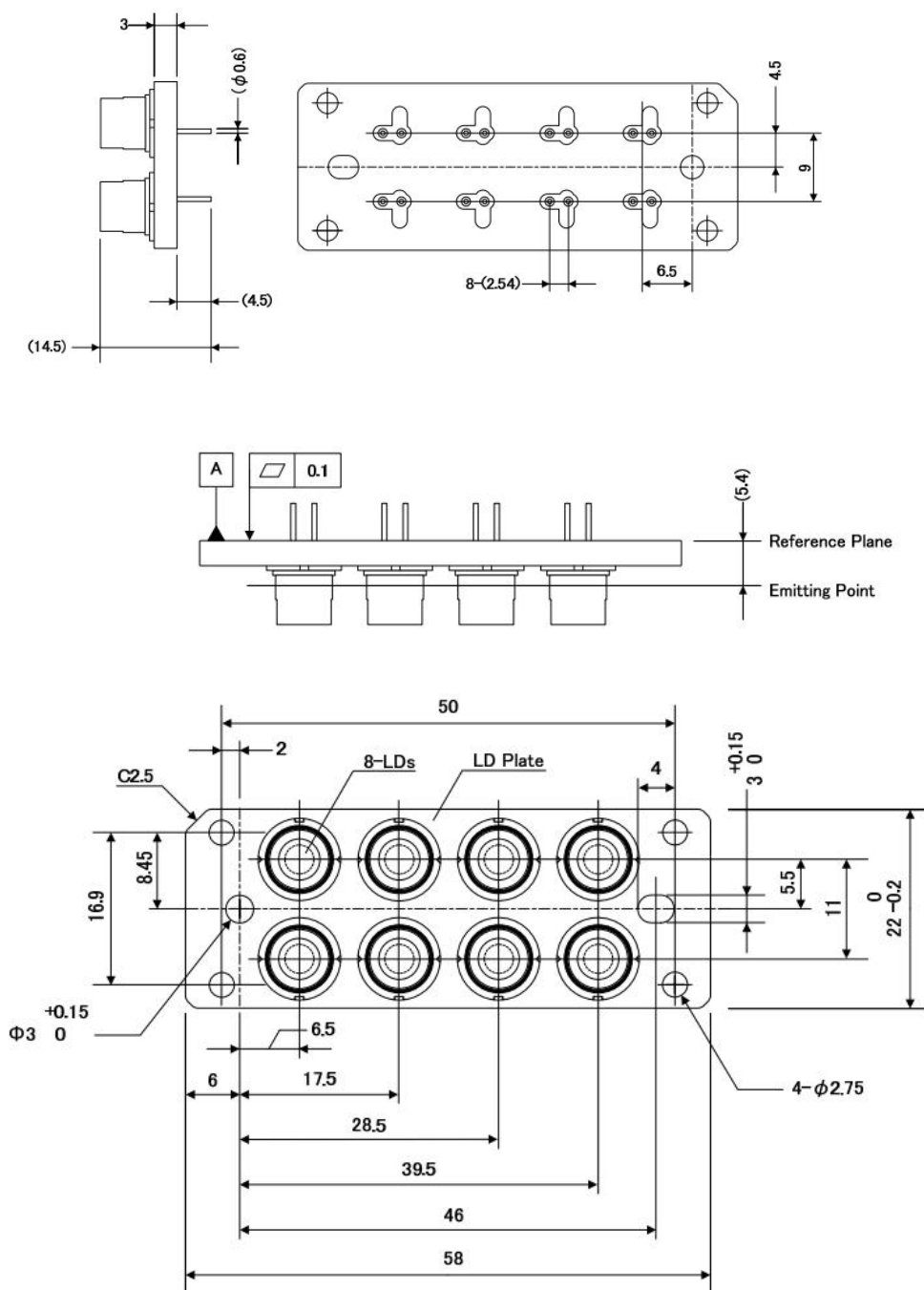
■ Initial Electrical/Optical Characteristics of mounted LD (T_c=25°C)

Parameter		Symbol	Condition	Min	Typ.	Max	Unit
Optical Output Power		P _o	I _f = 3.0A	-	(4.1)	-	W
Dominant Wavelength		λ _d	I _f = 3.0A	518	(525)	532	nm
Threshold Current		I _{th}	CW	150	-	500	mA
Slope Efficiency		η	CW	-	1.1	-	W/A
Operating Voltage		V _{op}	I _f = 3.0A	4.0	-	5.5	V
Beam Divergence *	Parallel	θ _{//}	I _f = 3.0A	0.2	0.4	0.6	°
	Perpendicular	θ _⊥	I _f = 3.0A	-1.0	0	1.0	°

() are reference figures.

* Full angle at 1/e² from peak intensity.

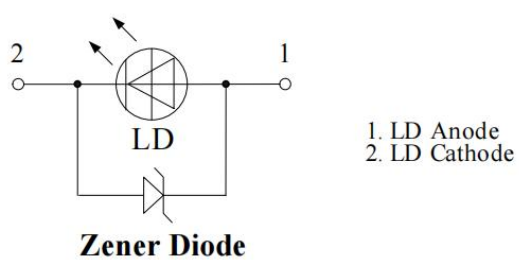
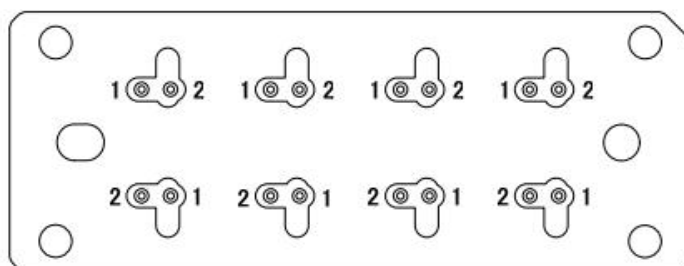
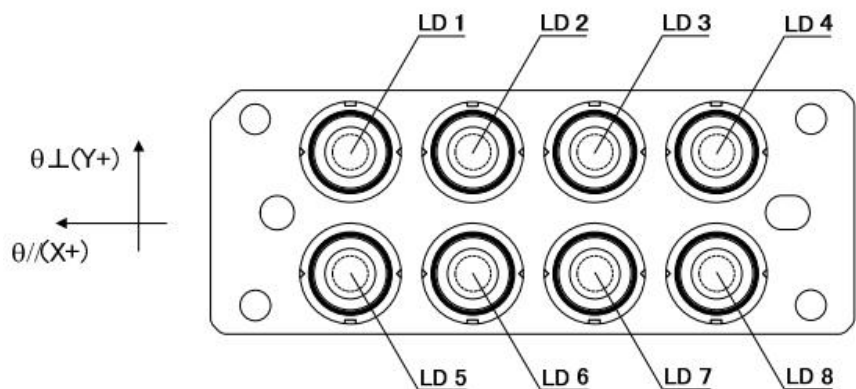
■ Outline Dimension (Unit:mm)



Dimensions are in millimeters

Figures in () are reference purpose only.

■ LD Position No.& Pin connection



■ Cautions

1. Laser light can damage the human eye and skin. Do not expose the eye and skin to any laser light directly or through optical lenses. Focused laser beam through optical instruments will increase the chance of eye hazard.
2. The laser needs a stable driver to avoid surges. The instantaneous reverse current and reverse voltage should not exceed the absolute maximum ratings, otherwise it will damage the laser diode.
3. Semiconductor lasers are sensitive to temperature, working at high temperatures will reduce the photoelectric conversion efficiency and accelerate the aging of laser diode. It should be used under adequate heat dissipation or cooling conditions.
4. The laser should be used at the rated current and rated power, the output power is too high will accelerate the aging of laser diode.
5. Semiconductor lasers are electrostatic sensitive devices, anti-static measures should be taken during storage and transportation.
6. Lasers should be stored or work in a dry, ventilated environment to prevent damage to the laser from condensation.
7. The light emitting surface (cavity surface) is the key parts of the laser diode, any handling to damage the cavity surface should be strictly prohibited. It should be ensured that the laser diode is not contaminated, and damaged in mechanical.

